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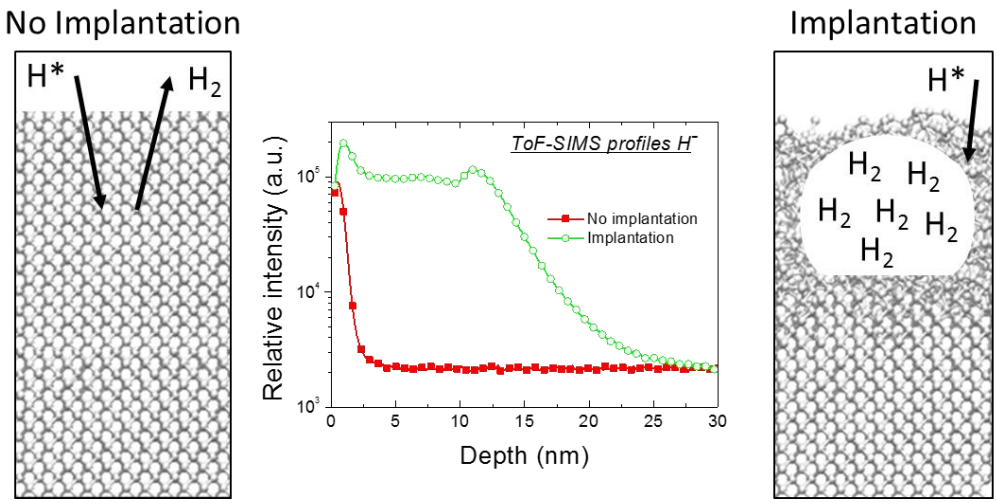
Graphical Abstract



Highlights

- The mechanism of blister formation in implanted silicon during H_2-based plasma dry strip processes is understood in correlation with SRIM simulation
- Influence of implantation parameters (dopant species, energy and dose) is investigated and compared to SRIM simulations
- Solution is proposed to delay blister formation